

Device Modeling Report

COMPONENTS:

DIODE/ GENERAL PURPOSE RECTIFIER / STANDARD

PART NUMBER: 20GL2C41A

MANUFACTURER: TOSHIBA

REMARK: TC= 110C

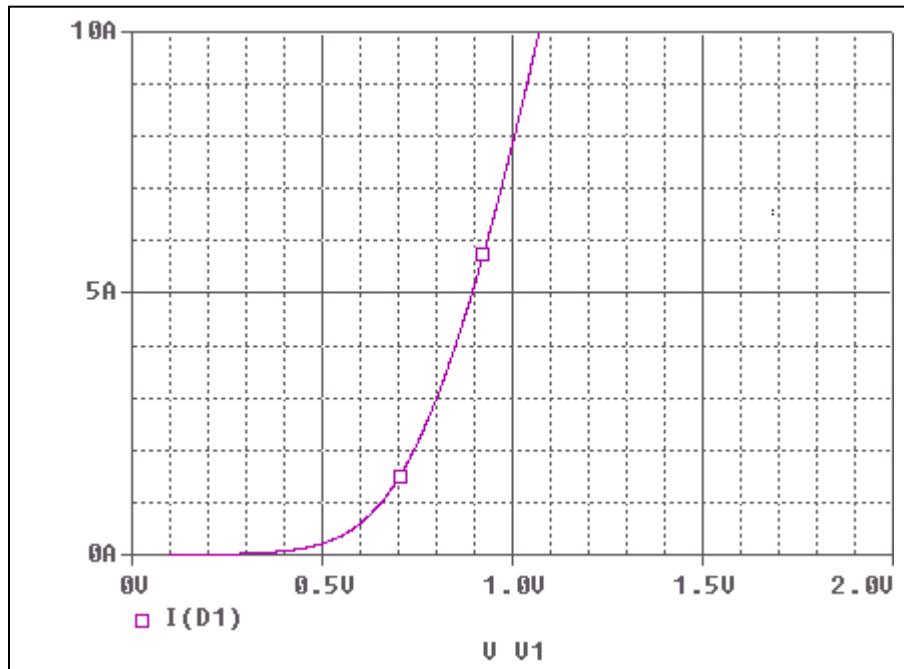


Bee Technologies Inc.

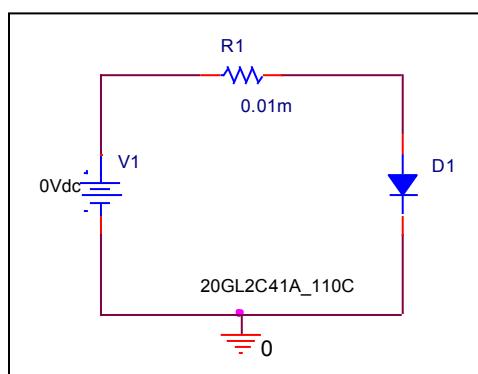
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

Circuit Simulation Result

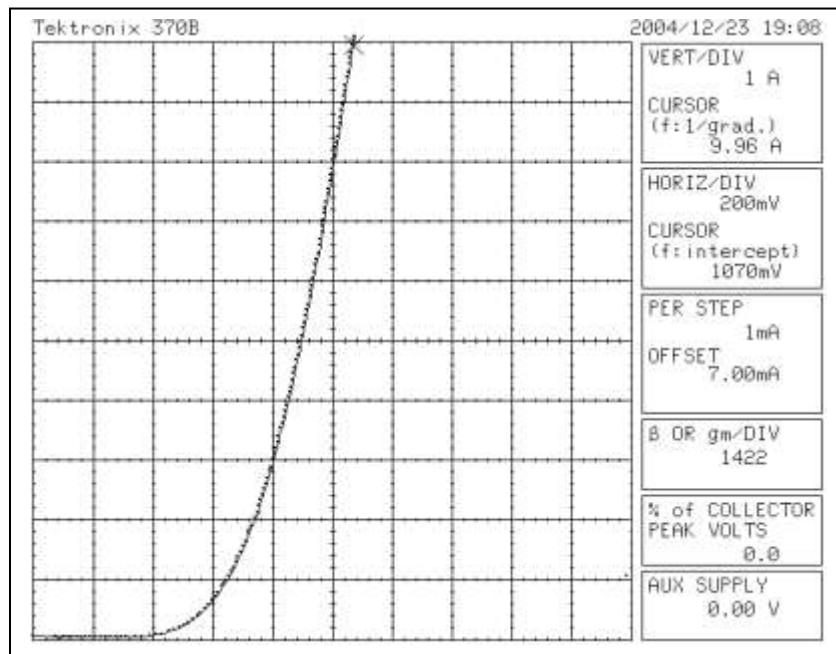


Evaluation Circuit



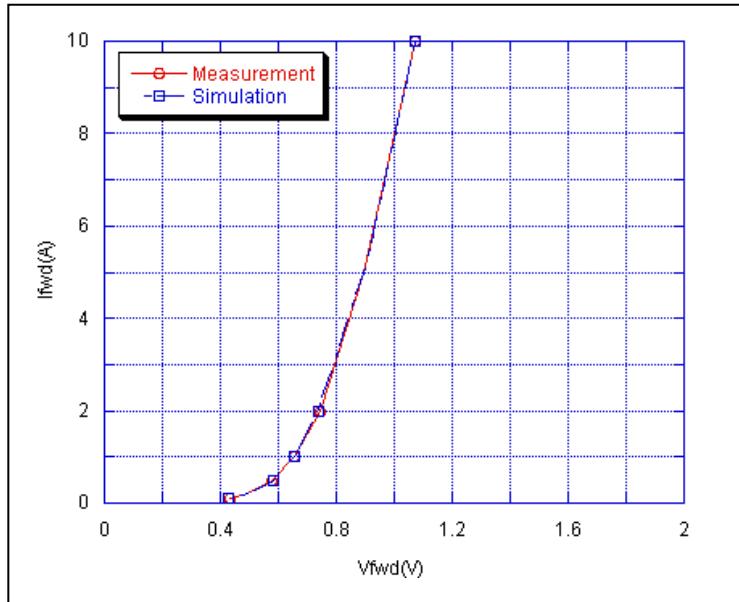
Forward Current Characteristic

Reference



Comparison Graph

Circuit Simulation Result

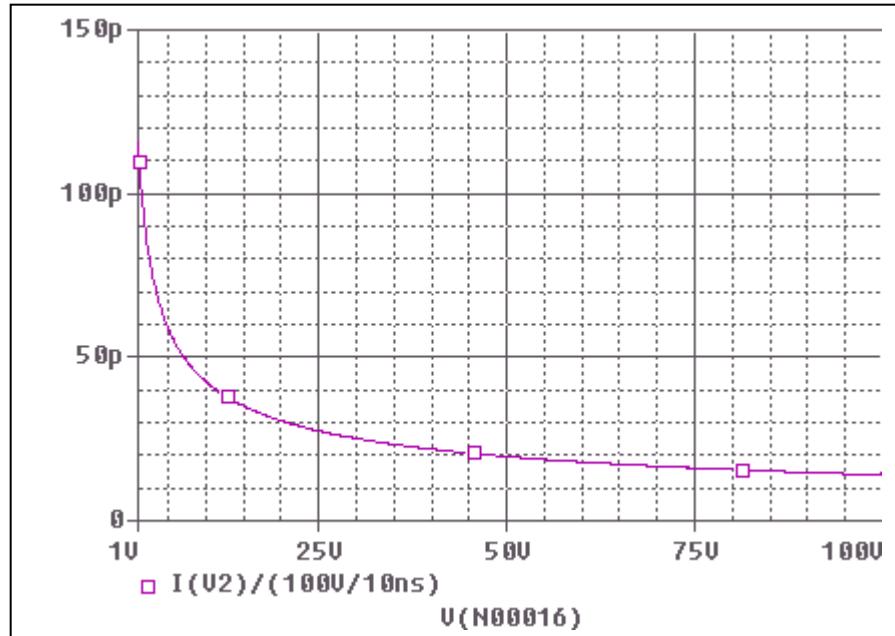


Simulation Result

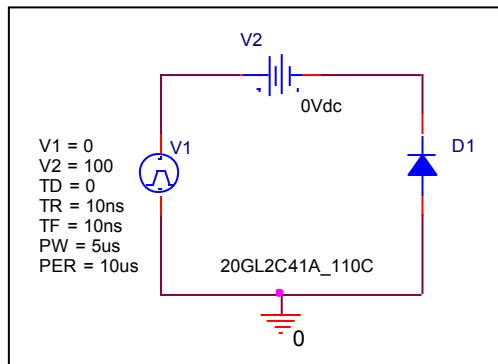
I_{fwd} (A)	V_{fwd} (V) Measurement	V_{fwd} (V) Simulation	%Error
0.1	0.432	0.430	0.532
0.2	0.492	0.493	-0.264
0.5	0.578	0.582	-0.606
1	0.656	0.655	0.137
2	0.744	0.740	0.538
5	0.892	0.894	-0.168
10	1.070	1.070	0.019

Capacitance Characteristic

Circuit Simulation Result

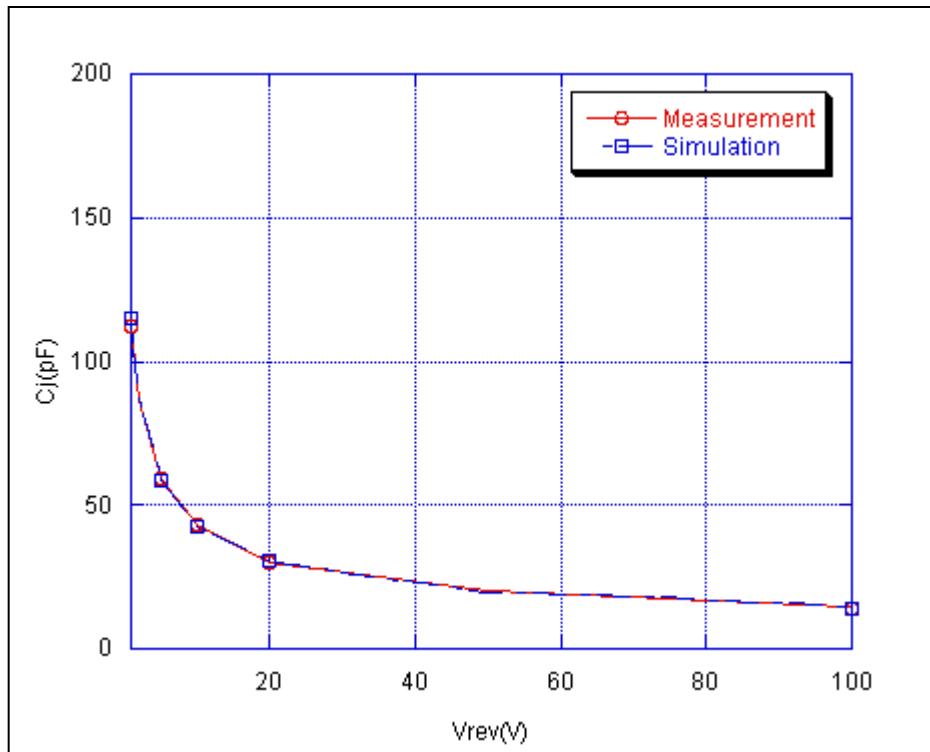


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

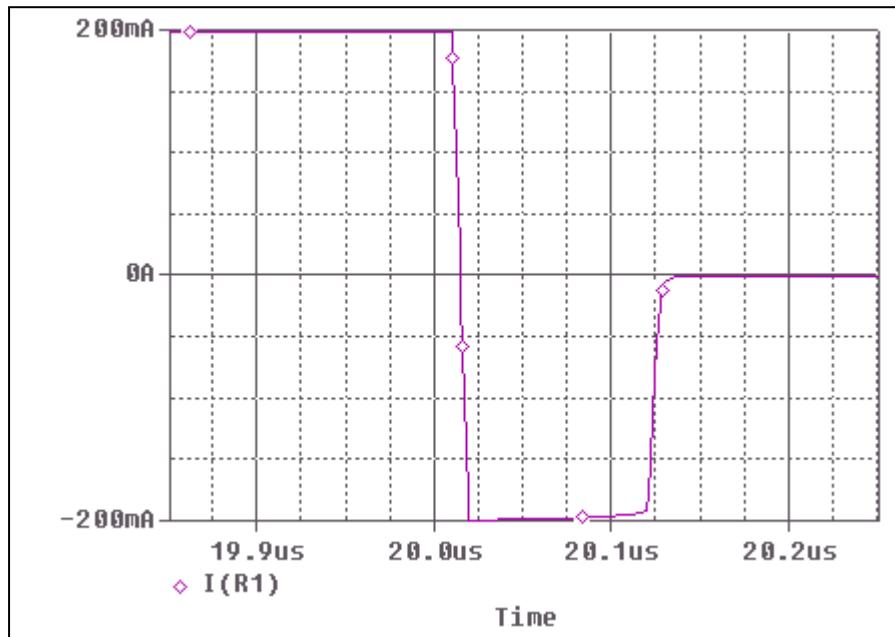


Simulation Result

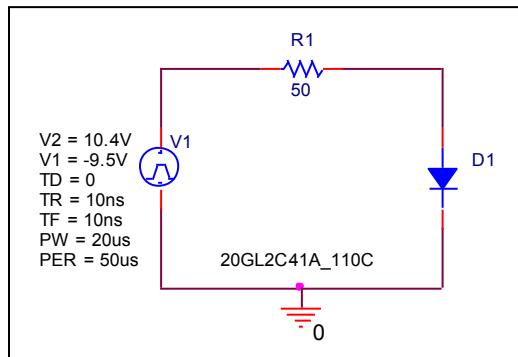
$V_{rev}(V)$	$C_j(pF)$ Measurement	$C_j(pF)$ Simulation	%Error
0	213.770	213.770	0.000
1	112.300	114.680	-2.119
2	86.710	87.880	-1.349
5	59.330	58.750	0.978
10	43.410	42.560	1.958
20	29.850	30.570	-2.412
50	20.170	19.630	2.677
100	14.160	14.090	0.494

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

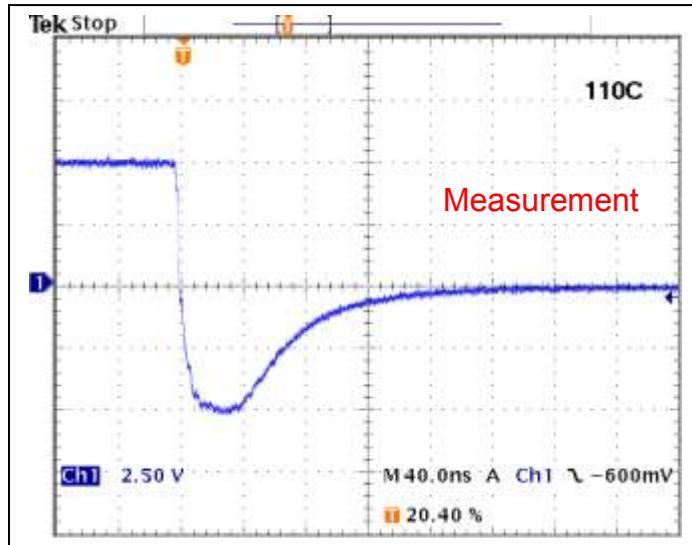


Compare Measurement vs. Simulation

	Measurement		Simulation		%Error
trr	121.60	ns	120.96	ns	0.526

Reverse Recovery Characteristic

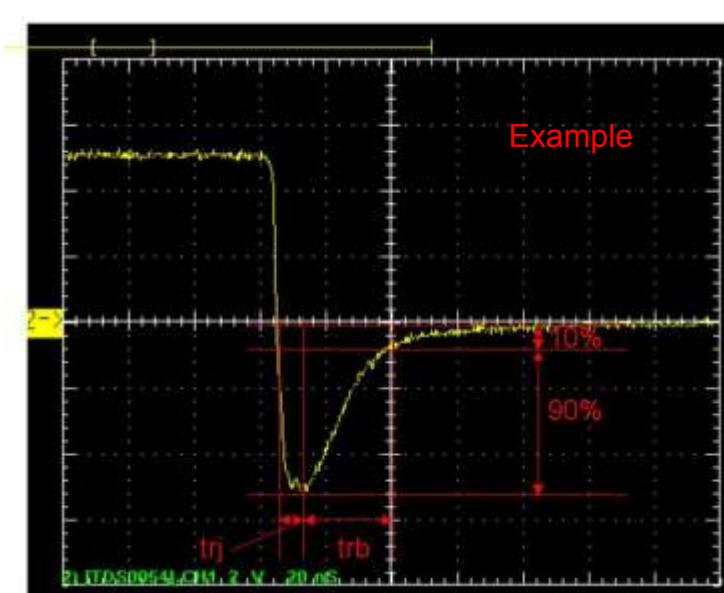
Reference



$Trj = 28(\text{ns})$

$Trb = 93.6(\text{ns})$

Conditions: $I_{fwd} = I_{rev} = 0.2(\text{A})$, $R_L = 5\Omega$



Relation between trj and trb